

2N2319 Transistors

Si NPN LP HF BJT

Military/High-Rel N

$V_{(BR)CEO}$ (V) 15

$V_{(BR)CBO}$ (V) 30

I_C Max. (A)

Absolute Max. Power Diss. (W) 300m

Maximum Operating Temp (\varnothing C) 200p

I_{CBO} Max. (A) 50n

@ V_{CBO} (V) (Test Condition) 20

h_{FE} Min. Current gain. 40

h_{FE} Max. Current gain.

@ I_C (A) (Test Condition) 20m

@ V_{CE} (V) (Test Condition) 400m

f_T Min. (Hz) Transition Freq 300M

@ I_C (A) (Test Condition) 10m

@ V_{CE} (V) (Test Condition) 10

V_{CEsat} Max. (V) .35

@ I_C (A) (Test Condition) 20m

@ I_B (A) (Test Condition) 1.0m

h_{fe} Min. SS Current gain. 3.0

@ I_C (A) (Test Condition) 10m α

@ V_{CE} (V) (Test Condition) 10